8-input NAND gate Rev. 04 — 4 May 2010

Product data sheet

1. General description

The 74HC30; 74HCT30 are high-speed Si-gate CMOS devices that comply with JEDEC standard no. 7A. They are pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC30; 74HCT30 provides a quad 8-input NAND function.

2. Features and benefits

- Input levels:
 - For 74HC30: CMOS level
 - ◆ For 74HCT30: TTL level
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

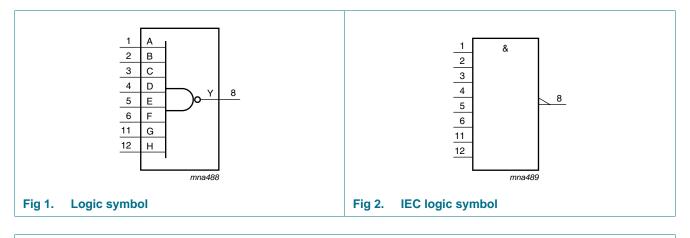
3. Ordering information

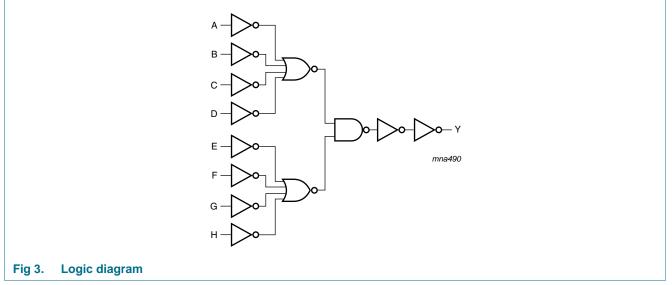
Table 1.Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC30N	–40 °C to +125 °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1
74HCT30N				
74HC30D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads;	SOT108-1
74HCT30D			body width 3.9 mm	
74HC30DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body	SOT337-1
74HCT30DB			width 5.3 mm	
74HC30PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads;	SOT402-1
74HCT30PW			body width 4.4 mm	



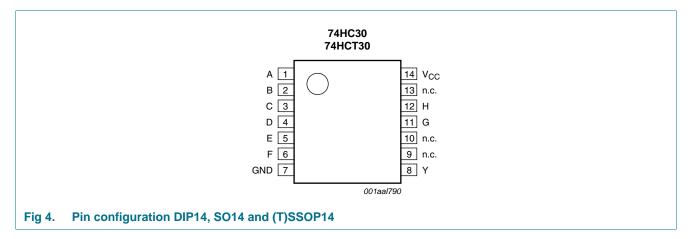
4. Functional diagram





5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2.	Pin description	
Symbol	Pin	Description
A	1	data input
В	2	data input
С	3	data input
D	4	data input
E	5	data input
F	6	data input
GND	7	ground (0 V)
Y	8	data output
n.c.	9	not connected
n.c.	10	not connected
G	11	data input
Н	12	data input
n.c.	13	not connected
V _{CC}	14	supply voltage

3 of 16

6. Functional description

Table 3. Function table^[1]

Input								Output
Α	В	С	D	Е	F	G	Н	Y
L	Х	Х	Х	Х	Х	Х	Х	Н
Х	L	Х	Х	Х	Х	Х	Х	Н
Х	Х	L	Х	Х	Х	Х	Х	Н
Х	Х	Х	L	Х	Х	Х	Х	Н
Х	Х	Х	Х	L	Х	Х	Х	Н
Х	Х	Х	Х	Х	L	Х	Х	Н
Х	Х	Х	Х	Х	Х	L	Х	Н
Х	Х	Х	Х	Х	Х	Х	L	Н
Н	Н	Н	Н	Н	Н	Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

				.0	,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_{\rm I} < -0.5$ V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
Ι _Ο	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation				
	DIP14 package		[2] _	750	mW
	SO14, (T)SSOP14 packages		[2] _	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For DIP14 package: P_{tot} derates linearly with 12 mW/K above 70 °C.

For SO14 package: P_{tot} derates linearly with 8 mW/K above 70 °C. For (T)SSOP14 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter Conditions		74HC30			74HCT30			Unit
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC30									1	
V _{IH}	HIGH-level	$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	-	1.8	V
V _{он}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_O = -20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.9	2.0	-	1.9	-	1.9	-	V
		I_{O} = -20 μ A; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_{O} = –20 $\mu A; V_{CC}$ = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_{O} = -4.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_{O} = -5.2 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	I_{O} = 20 μ A; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \ \mu\text{A}; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_{O} = 5.2 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	±0.1	-	±1	-	±1	μA
lcc	supply current		-	-	2.0	-	20	-	40	μA

Symbol	Parameter	Conditions		25 °C		−40 °C t	o +85 °C	–40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
Cı	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT3	0									
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
VIL	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±0.1	-	±1	-	±1	μΑ
I _{CC}	supply current		-	-	2.0	-	20	-	40	μΑ
ΔI _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.4 \text{ V}; I_O = 0 \text{ A};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	60	216	-	275	-	294	μA
CI	input capacitance		-	3.5	-	-	-	-	-	pF

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

10. Dynamic characteristics

Table 7. Dynamic characteristics

 $GND = 0 V; C_L = 50 pF;$ for load circuit see <u>Figure 6</u>.

Symbol	Parameter	Conditions		25 °C			−40 °C to +125 °C		Unit
				Min	Тур	Max	Max (85 °C)	Max (125 °C)	
74HC30									
t _{pd}	propagation delay	A, B, C, D, E, F, G, H to Y; see <u>Figure 5</u>	<u>[1]</u>						
		$V_{CC} = 2.0 V$		-	41	130	165	195	ns
		$V_{CC} = 4.5 V$		-	15	26	33	39	ns
		V_{CC} = 5.0 V; C_{L} = 15 pF		-	12	-	-	-	ns
		$V_{CC} = 6.0 V$		-	12	22	28	33	ns
t _t	transition time	see Figure 5	[2]						
		$V_{CC} = 2.0 V$		-	19	75	95	110	ns
		$V_{CC} = 4.5 V$		-	7	15	19	22	ns
		$V_{CC} = 6.0 V$		-	6	13	16	19	ns

74HC_HCT30_4
Product data sheet

Symbol	Parameter	Conditions			25 °C		–40 °C to	Unit	
				Min	Тур	Max	Max (85 °C)	Max (125 °C)	
C _{PD}	power dissipation capacitance	per package; $V_I = GND$ to V_{CC}	<u>[3]</u>	-	15	-	-	-	pF
74HCT30)								
t _{pd}	propagation delay	A, B, C, D, E, F, G, H to Y; see <u>Figure 5</u>	<u>[1]</u>						
		$V_{CC} = 4.5 V$		-	16	28	35	42	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	12	-	-	-	ns
t _t	transition time	V_{CC} = 4.5 V; see <u>Figure 5</u>	[2]	-	7	15	19	22	ns
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} – 1.5 V	[3]	-	15	-	-	-	pF

Table 7. Dynamic characteristics ... continued GND = 0 V: $C_1 = 50$ pF: for load circuit see Figure 6.

 $\label{eq:tpd} [1] \quad t_{pd} \text{ is the same as } t_{PHL} \text{ and } t_{PLH}.$

[2] t_t is the same as t_{THL} and t_{TLH} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W):

 P_{D} = $C_{PD} \times V_{CC}{}^2 \times f_i \times N$ + Σ ($C_{L} \times V_{CC}{}^2 \times f_o$) where:

 f_i = input frequency in MHz;

 f_o = output frequency in MHz;

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$

11. Waveforms

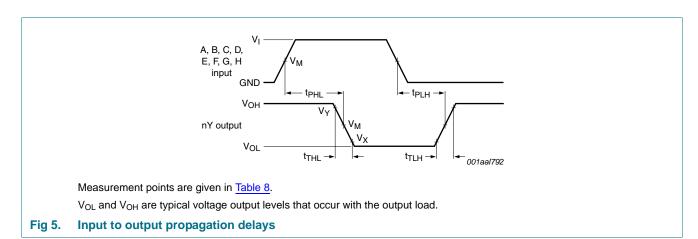


Table 8.Measurement points

Туре	Input	Output					
	V _M	V _M	V _X	V _Y			
74HC30	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}			
74HCT30	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}			

NXP Semiconductors

74HC30; 74HCT30

8-input NAND gate

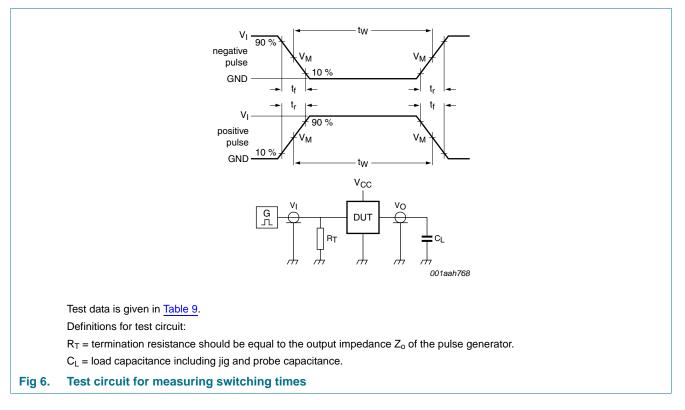


Table 9. Test data

Туре	Input L		Load	Test
	VI	t _r , t _f	CL	
74HC30	V _{CC}	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}
74HCT30	3.0 V	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}

74HC30; 74HCT30

8-input NAND gate

12. Package outline

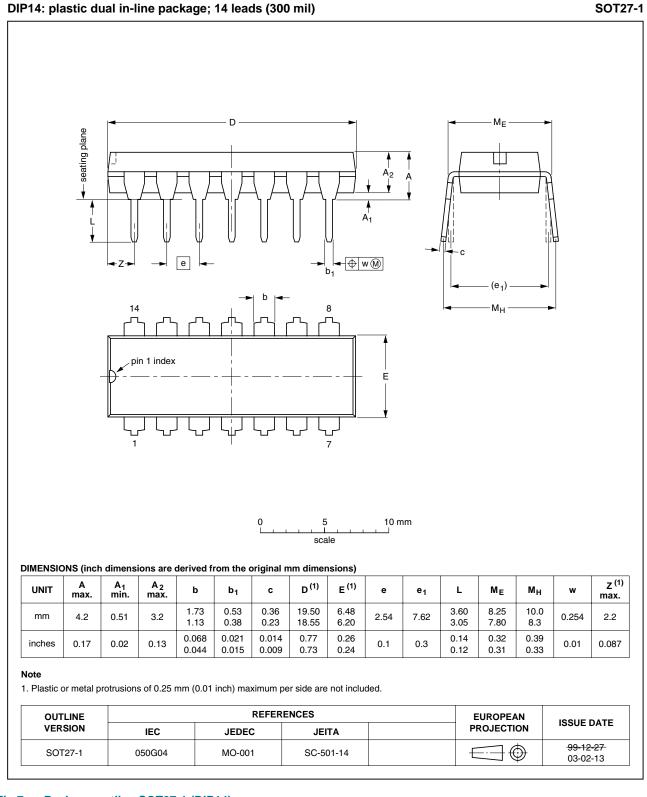
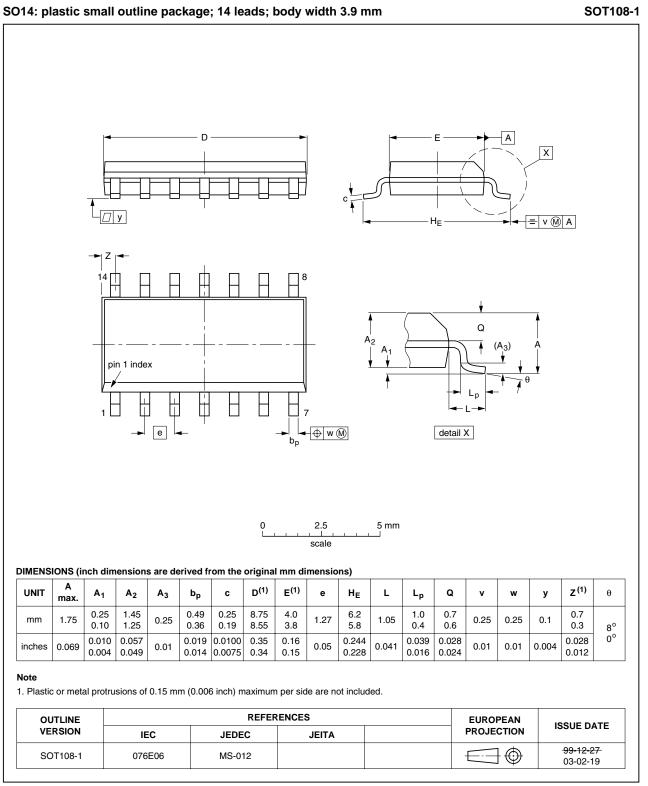


Fig 7. Package outline SOT27-1 (DIP14)

All information provided in this document is subject to legal disclaimers.



Package outline SOT108-1 (SO14) Fig 8.

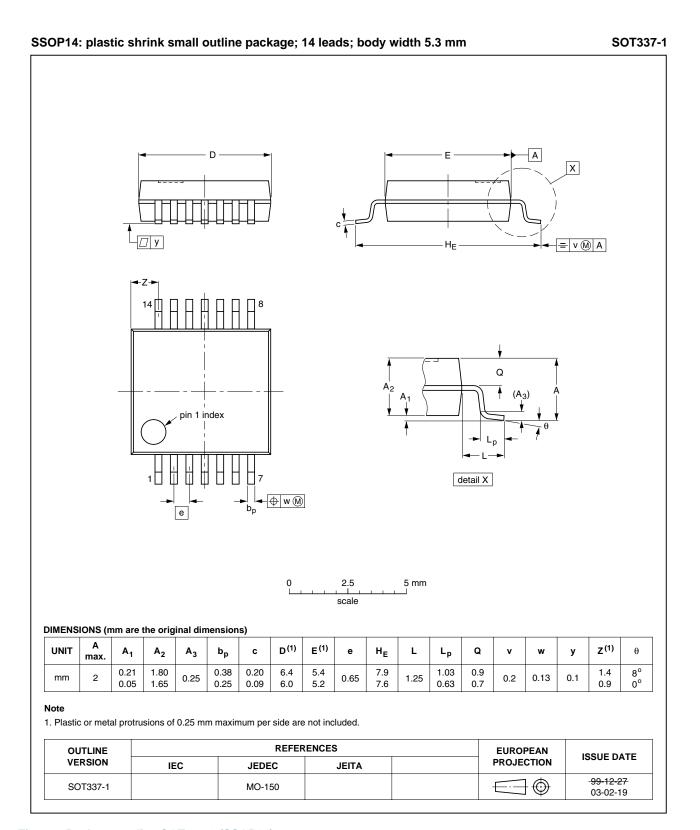


Fig 9. Package outline SOT337-1 (SSOP14)

All information provided in this document is subject to legal disclaimers.

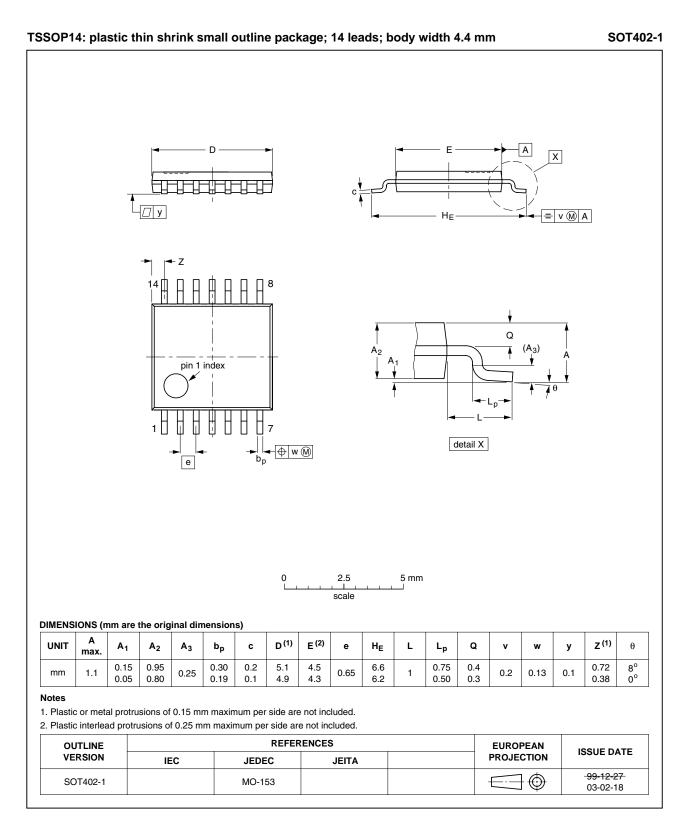


Fig 10. Package outline SOT402-1 (TSSOP14)

All information provided in this document is subject to legal disclaimers.

13. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT30_4	20100504	Product data sheet	-	74HC_HCT30_3
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 			
	 Legal texts h 	ave been adapted to the new	company name whe	re appropriate.
74HC_HCT30_3	20100420	Product data sheet	-	74HC_HCT30_2
74HC_HCT30_2	19970829	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

15.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

15.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This NXP Semiconductors product has been qualified for use in automotive applications. The product is not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Product data sheet

74HC HCT30 4

74HC30; 74HCT30

8-input NAND gate

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

15.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

16. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

74HC30; 74HCT30

17. Contents

1	General description 1
2	Features and benefits 1
3	Ordering information 1
4	Functional diagram 2
5	Pinning information 3
5.1	Pinning 3
5.2	Pin description 3
6	Functional description 4
7	Limiting values 4
8	Recommended operating conditions 5
9	Static characteristics 5
10	Dynamic characteristics 6
11	Waveforms 7
12	Package outline 9
13	Abbreviations 13
14	Revision history 13
15	Legal information 14
15.1	Data sheet status 14
15.2	Definitions 14
15.3	Disclaimers
15.4	Trademarks 15
16	Contact information 15
17	Contents 16

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2010.

All rights reserved.

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 4 May 2010 Document identifier: 74HC_HCT30_4